

# SKCD 43 C 120 I4



## CAL-DIODE

$I_F = 75 \text{ A}$

$V_{RRM} = 1200 \text{ V}$

Size: 6,55 mm x 6,55 mm

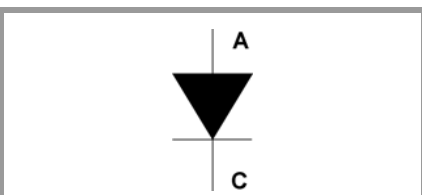
### SKCD 43 C 120 I4

#### Features

- max. junction 175 °C
- very low forward voltage drop
- positive temperature coefficient
- extreme soft recovery

#### Typical Applications\*

- freewheeling diode for IGBT



SKCD

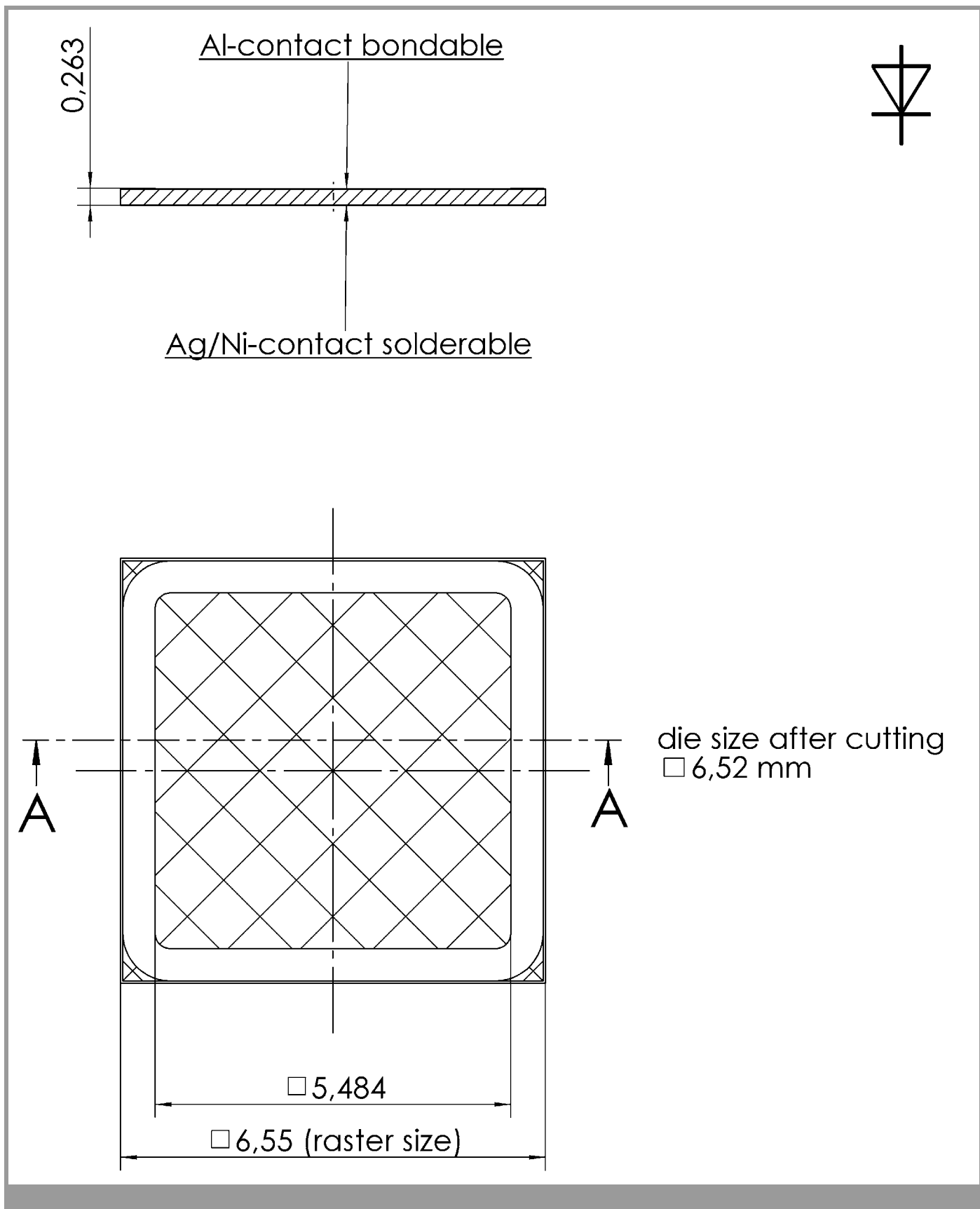
Absolute Maximum Ratings			
Symbol	Conditions	Values	Unit
$V_{RRM}$	$T_j = 25 \text{ °C}, I_R = 0.12 \text{ mA}$	1200	V
$I_{F(AV)}$	$T_c = 80 \text{ °C}, T_j = 175 \text{ °C}, F_i = PI/2$	48	A
$I_{FSM}$	10 ms	$T_j = 25 \text{ °C}$	A
	sin 180°	$T_j = 150 \text{ °C}$	A
$T_{jmax}$		175	°C

Electrical Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
$i^2t$	$T_j = 150 \text{ °C}, \text{sin } 180^\circ, 10 \text{ ms}$			925	A <sup>2</sup> s
$I_R$	$T_j = 25 \text{ °C}, V_{RRM} = 1200 \text{ V}$			0.12	mA
	$T_j = 150 \text{ °C}, V_{RRM} = 1200 \text{ V}$		7.00	14.00	mA
$V_F$	$T_j = 25 \text{ °C}, I_F = 75 \text{ A}$		2.17	2.49	V
	$T_j = 150 \text{ °C}, I_F = 75 \text{ A}$		2.11	2.42	V
	$T_j = 175 \text{ °C}, I_F = 75 \text{ A}$		1.96	2.27	V
$V_{(TO)}$	$T_j = 150 \text{ °C}$		0.90	1.10	V
$r_T$	$T_j = 150 \text{ °C}$		16.1	17.70	mΩ
$V_{(TO)}$	$T_j = 175 \text{ °C}$		0.82	0.98	V
$r_T$	$T_j = 175 \text{ °C}$		15.20	17.30	mΩ

Dynamic Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
$t_{rr}$	$T_j = 150 \text{ °C}, 75 \text{ A}, 600 \text{ V}, 1500 \text{ A}/\mu\text{s}$		0.5		μs
$E_{rr}$	$T_j = 150 \text{ °C}, 75 \text{ A}, 600 \text{ V}, 1500 \text{ A}/\mu\text{s}$		4.2		mJ
$I_{rrm}$	$T_j = 150 \text{ °C}, 75 \text{ A}, 600 \text{ V}, 1500 \text{ A}/\mu\text{s}$		58		A

Thermal Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
$T_j$		-40		175	°C
$T_{stg}$		-40		175	°C
$T_{solder}$	10 min.			250	°C
$T_{solder}$	5 min.			320	°C
$R_{th(j-c)}$	Semitrans Assembly		0.66		K/W

Mechanical Characteristics			
Symbol	Conditions	Values	Unit
Raster size		6.55 x 6.55	mm <sup>2</sup>
Area total		43	mm <sup>2</sup>
Anode	Metallization	bondable (Al)	
Cathode	Metallization	solderable (Ag/Ni)	
Wire bond		Al, typ. diameter = 300 μm	
Package		wafer frame	
Chips / Package		337	pcs



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.